

AP09N70R

RoHS-compliant Product

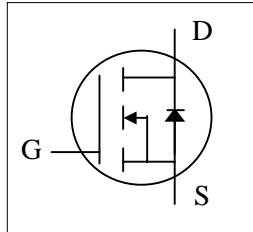


**Advanced Power
Electronics Corp.**

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

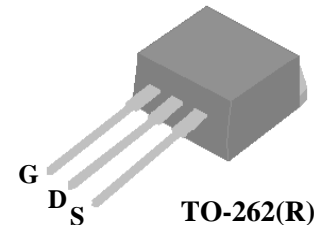
- ▼ 100% Avalanche Rated
- ▼ Fast Switching
- ▼ Simple Drive Requirement



BV_{DSS}	600V
$R_{DS(ON)}$	0.75 Ω
I_D	9A

Description

AP09N70 series are specially designed as main switching devices for universal 90~265VAC off-line AC/DC converter applications. The TO-262 type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	9	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	5	A
I_{DM}	Pulsed Drain Current ¹	40	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	156	W
E_{AS}	Single Pulse Avalanche Energy ²	305	mJ
I_{AR}	Avalanche Current	9	A
E_{AR}	Repetitive Avalanche Energy	9	mJ
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	0.8	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ C/W$



Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	600	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ³	V _{GS} =10V, I _D =4.5A	-	-	0.75	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =4.5A	-	4.5	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V, V _{GS} =0V	-	-	25	uA
	Drain-Source Leakage Current (T _j =125°C)	V _{DS} =480V, V _{GS} =0V	-	-	500	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ³	I _D =9A	-	44	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} =480V	-	11	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	12	-	nC
t _{d(on)}	Turn-on Delay Time ³	V _{DD} =300V	-	19	-	ns
t _r	Rise Time	I _D =9A	-	21	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =10Ω, V _{GS} =10V	-	56	-	ns
t _f	Fall Time	R _D =34Ω	-	24	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	2660	-	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	170	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	10	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _S	Continuous Source Current (Body Diode)	V _D =V _G =0V , V _S =1.5V	-	-	9	A
I _{SM}	Pulsed Source Current (Body Diode) ¹		-	-	40	A
V _{SD}	Forward On Voltage ³	T _j =25°C, I _S =9A, V _{GS} =0V	-	-	1.5	V

Notes:

- 1.Pulse width limited by Maximum junction temperature.
- 2.Starting T_j=25°C , V_{DD}=50V , L=6.8mH , R_G=25Ω , I_{AS}=9A.
- 3.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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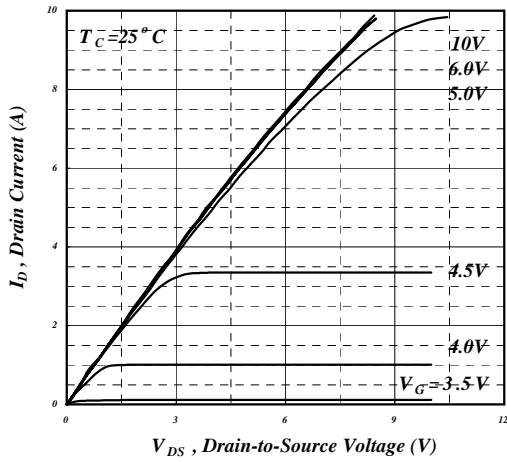


Fig 1. Typical Output Characteristics

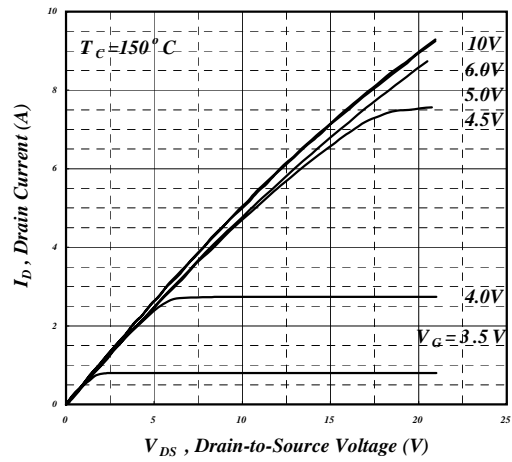


Fig 2. Typical Output Characteristics

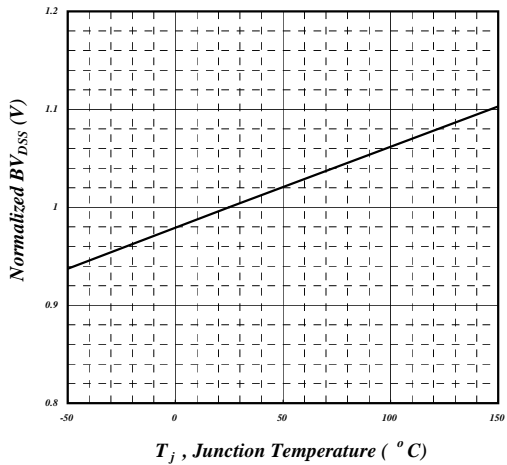


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

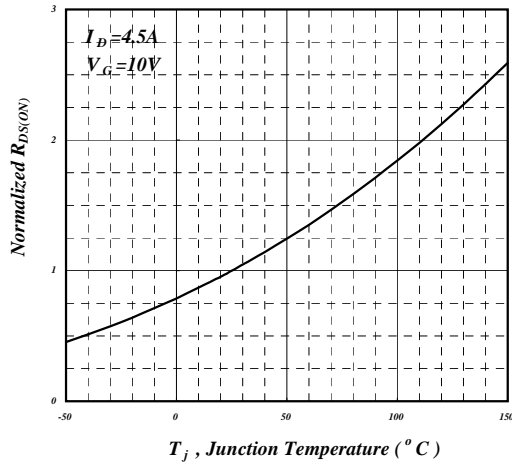


Fig 4. Normalized On-Resistance v.s. Junction Temperature

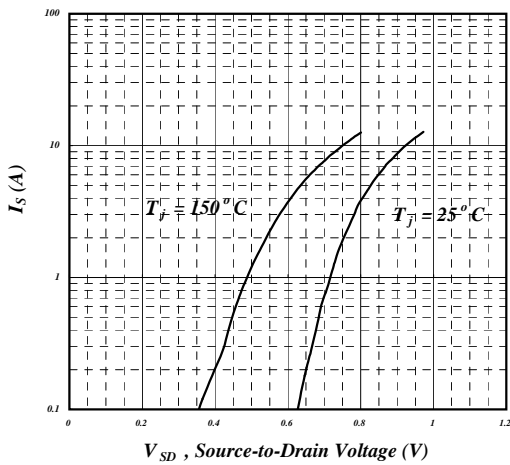


Fig 5. Forward Characteristic of Reverse Diode

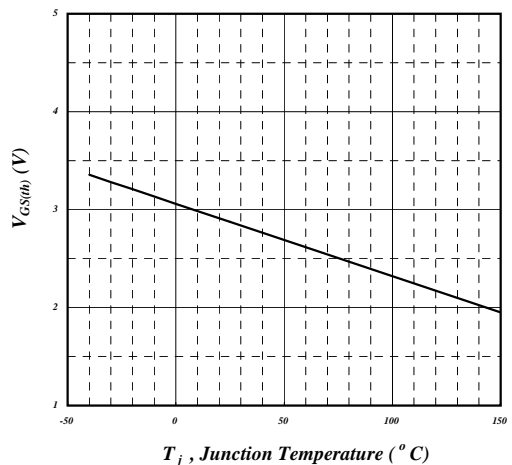


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

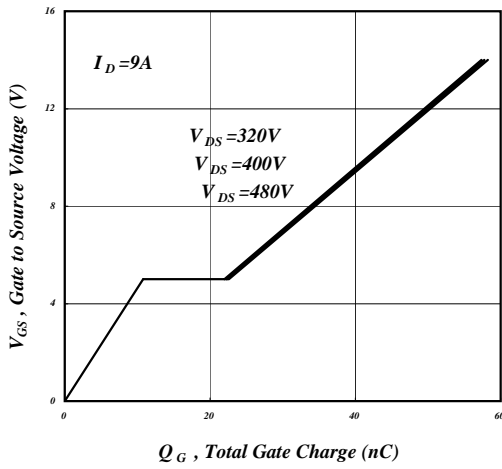


Fig 7. Gate Charge Characteristics

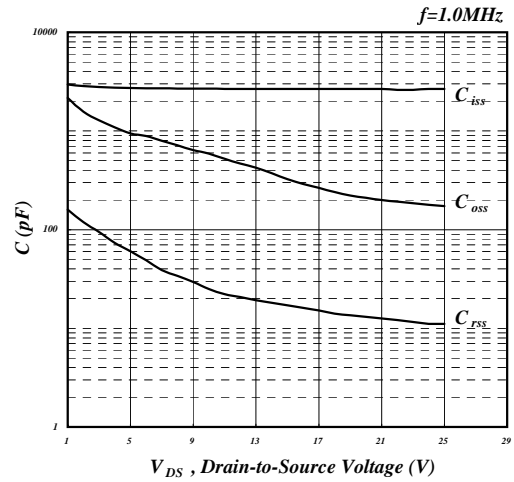


Fig 8. Typical Capacitance Characteristics

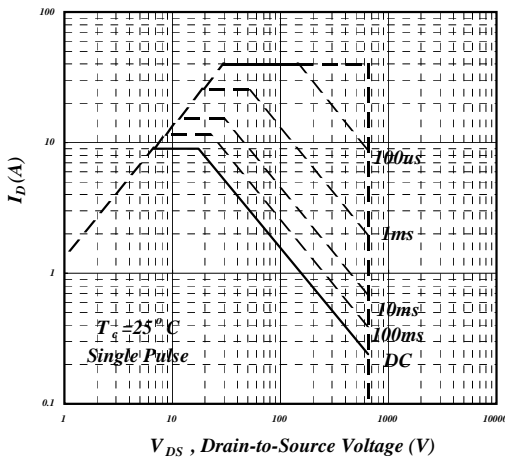


Fig 9. Maximum Safe Operating Area

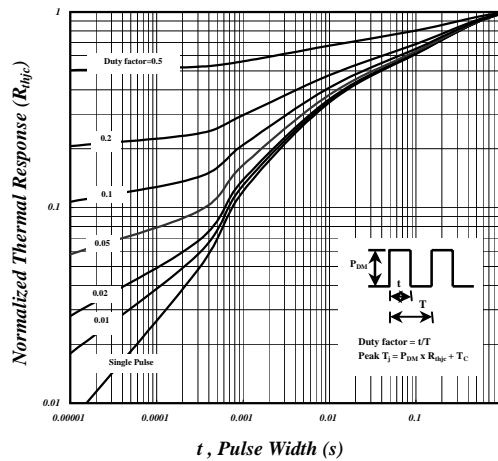


Fig 10. Effective Transient Thermal Impedance



Fig 11. Switching Time Waveform

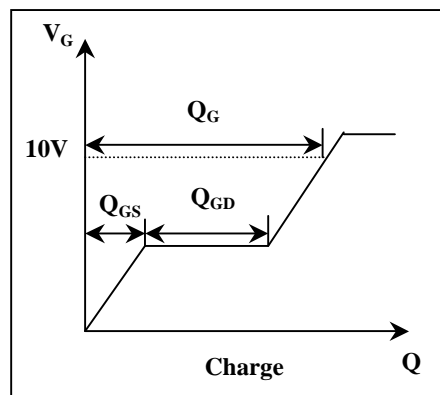


Fig 12. Gate Charge Waveform